

FOTOFET™
SILICON EPITAXIAL JUNCTION
N-CHANNEL FIELD EFFECT TRANSISTOR

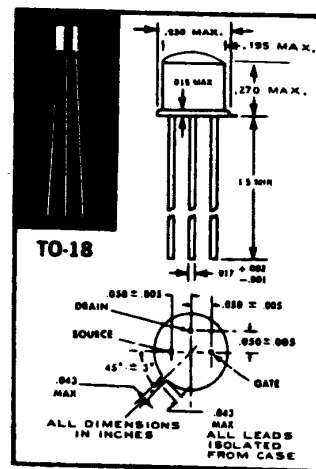
FF412

GEOMETRY 446

- HIGH SENSITIVITY
- LOW DARK CURRENT
- FAST RESPONSE
- LOW R_{ON}

ELECTRICAL DATA ABSOLUTE MAXIMUM RATING

Drain to Source Voltage	BV_{DSO}	30 Volts
Drain to Gate Voltage	BV_{DGO}	30 Volts
Gate to Source Voltage	BV_{GSO}	-15 Volts
D.C. Forward Gate Current	I_{GF}	50 mA
Junction Temp (operating and storage)	T_J	-65°C to +200°C
Power Dissipation (free air)	P_D	300mW
Lead Temp (@1/16" ± 1/32" from case)	T_L	240°C for 10 sec.
Derating Factor From 200°C	DF	1.7mW/°C



TO-18
 ALL DIMENSIONS IN INCHES
 ALL LEADS ISOLATED FROM CASE
 ACTIVE AREA 0.0009 SQ. CM.
 AT DIE SURFACE SENSITIVITY $\approx 3\mu A/\mu W$

ELECTRICAL CHARACTERISTICS: $T_A = 25^\circ C$

PARAMETER	SYMBOL	CONDITION	FF412			Units
			Min.	Typ.	Max.	
Gate Sensitivity ⁵	S_G	$V_{DS} = 15V, V_{GS} = 0, \lambda = .9 \text{ microns}$	5.0	7.5	—	$\mu A/mW/cm^2$
Gate Current (Light) ¹	I_{IG}	$V_{DS} = 15V, V_{GS} = 0V$	8.0	12.0	—	nA/FC
Drain Sensitivity ⁶	S_D	$V_{DS} = 15V, I_D = 5mA, R_G = 1M\Omega$	—	90	—	$mA/mW/cm^2$
Drain Current (Light) ¹	I_{ID}	$V_{DS} = 15V, I_D = 5mA, R_G = 1M\Omega$	—	144	—	$\mu A/FC$
Zero Gate Voltage Drain Current ⁴	I_{DSS}	$V_{DS} = 15V, V_{GS} = 0$	5.0	35	—	mA
Transconductance	g_m	$V_{DS} = 15V, I_D = 5mA, f = 1kHz$	8,000	15,000	25,000	μmho
Rise Time ²	T_R	$V_{DS} = 15V, R_L = 1K, R_G = 1K$	—	25	—	nsec
Fall Time ³	T_F	$V_{DS} = 15V, R_L = 1K, R_G = 1K$	—	40	—	nsec
Pinch-Off Voltage	V_{PO}	$V_{DS} = 25V, I_{DS} = 10.0 \text{ nA}$	1.0	3.0	5.0	Volts
Gate to Source Cap.	C_{GS}	$V_{GS} = -10V, f = 140 \text{ kHz}$	—	—	6.5	pf
Gate to Drain Cap.	C_{GD}	$V_{GD} = -10V, f = 140 \text{ kHz}$	—	—	6.5	pf
Gate Leakage Current (Dark)	I_{GSS}	$V_{GS} = -5V, V_{DS} = 25$	—	0.05	1.0	nA
ON Resistance	R_{DS}	$V_{DS} = 0.1V, V_{GS} = 0$	—	50	100	Ohms

¹ Tungsten Lamp 2800° k Color Temp.

² GaAs Diode Source.

³ Directly Proportional to R_G

⁴ Pulse Measurement 1% Duty Cycle, 10MS Max.

⁵ Gate Current per unit Radiant Power Density at Lens Surface

⁶ Drain Current per unit Radiant Power Density ($\lambda = 0.9 \text{ microns}$)

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